BORN SEMICONDUCTOR

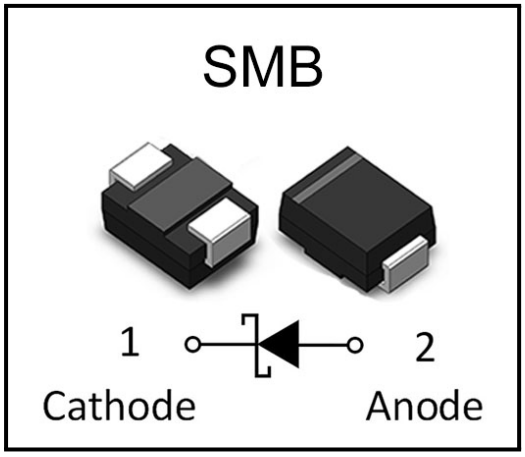
SS22-SS220

Schottky Barrier Diode

Features

- For surface mounted applications
- Matal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- Buit-in strain relief,ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

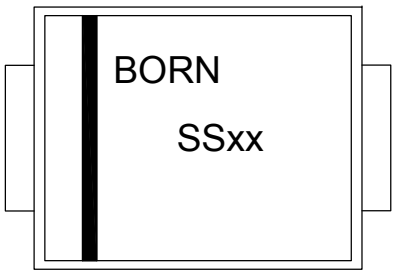
Package



Description

- Case: JEDEC DO-214AA molded plastic
- Terminals:Axial leads.Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position:Any

Marking



Ordering information

Part Number	SS22	SS23	SS24	SS25	SS26	SS28	SS29	SS210	SS215	SS220
Marking	SS22	SS23	SS24	SS25	SS26	SS28	SS29	SS210	SS215	SS220
Base qty	3K	3K	3K	3K	3K	3K	3K	3K	3K	3K

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SS22-SS220

Schottky Barrier Diode

Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 22	SS 23	SS 24	SS 25	SS 26	SS 28	SS 29	SS 210	SS 215	SS 220	Units
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	20	30	40	50	60	80	90	100	150	200	V
$V_{R(RMS)}$	Maximum RMS Reverse Voltage	14	21	28	35	42	56	63	70	105	140	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	90	100	150	200	V
$I_{F(AV)}$	Maximum average forward Rectified Current	2.0										A
I_{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	50										A
V_F	Maximum Instantaneous Forward Voltage @I_F=2.0A	0.55			0.70		0.85			0.95		V
I_R	Maximum DC Reverse current T_A=25°C	0.50					0.10					mA
	at Rated DC Blocking Voltage T_A=100°C	10					5					
T_J	Operating Temperature Range	-55 to +150										°C
T_{STG}	Storage Temperature Range	-55 to +150										°C
$R_{\theta JA}$	Thermal Resistance(1)	75										°C/W
$R_{\theta JL}$		17										

Note:(1)Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2” x 0.2” (5.0 mm x 5.0 mm) copper pad areas

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SS22-SS220

Schottky Barrier Diode

Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

Figure 1:I_O-T_L Curve

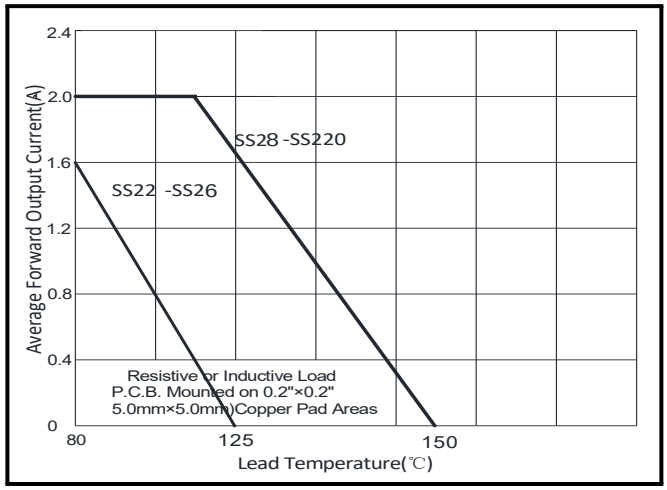


Figure 2:Surge Forward Current Capability

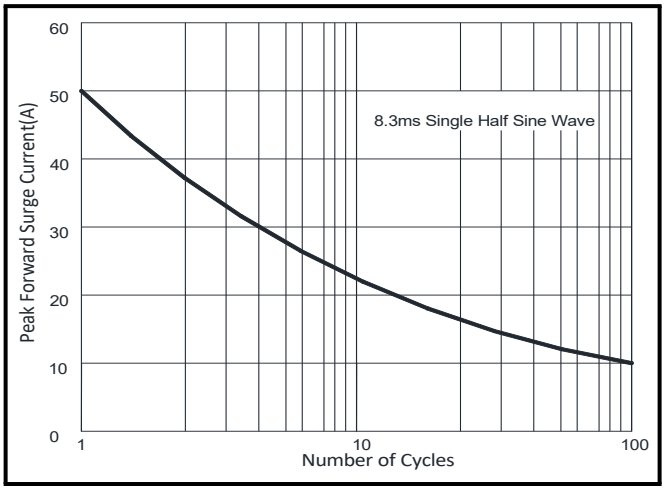


Figure 3:Forward Voltage

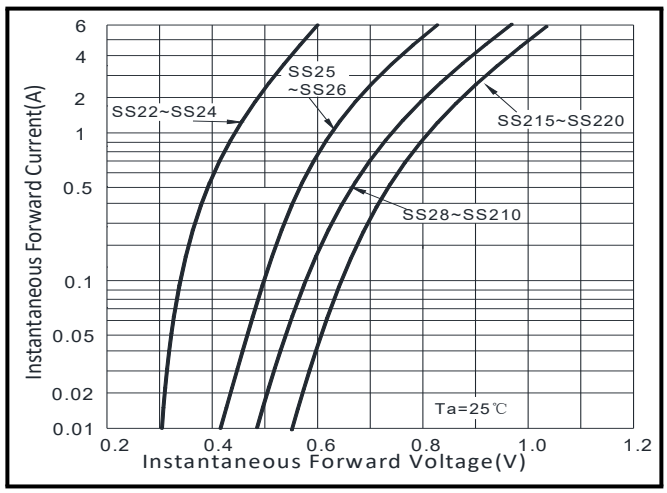
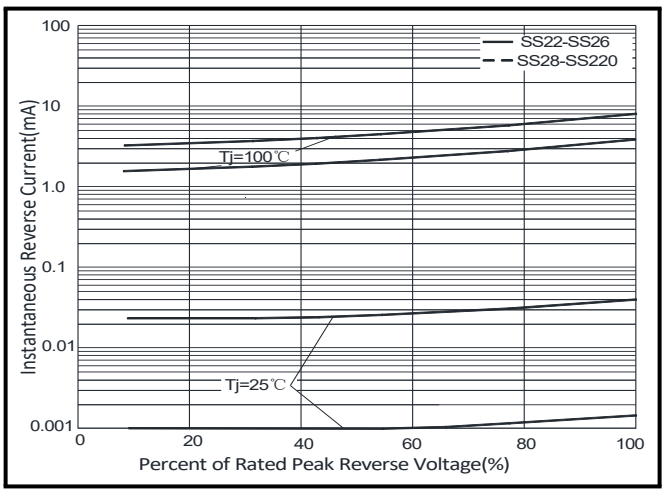


Figure 4:Typical Reverse Characteristics



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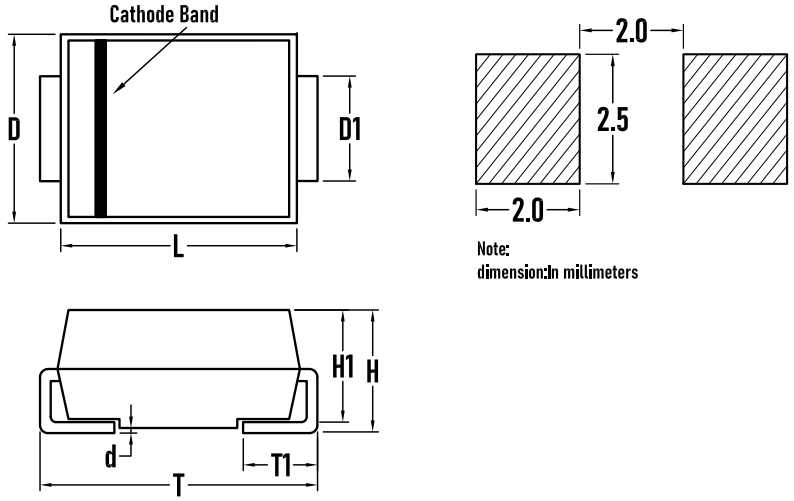
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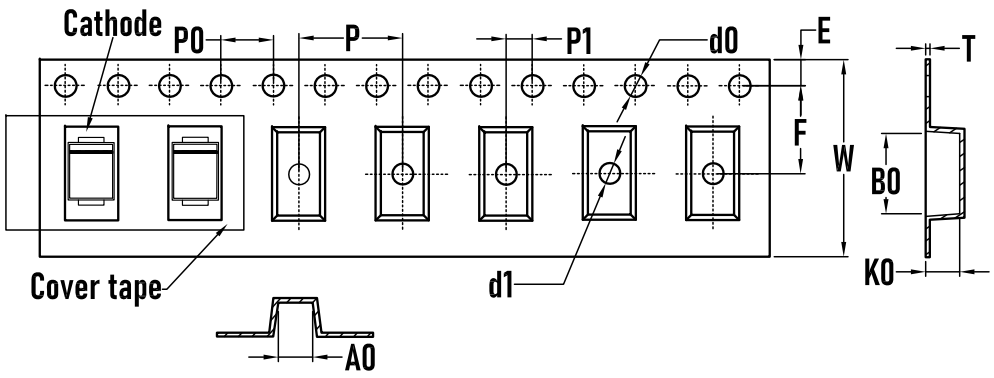
Schottky Barrier Diode

Outline Drawing - SMB



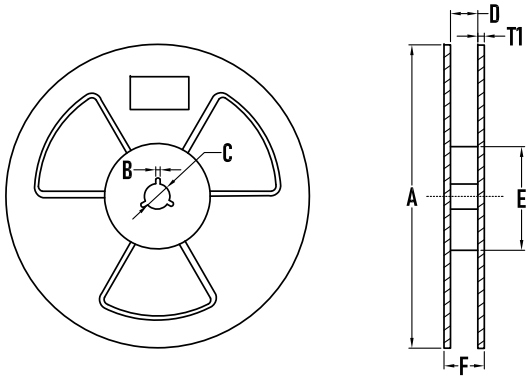
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	3.3	3.9	0.130	0.154
D1	1.7	2.3	0.067	0.091
T	5.1	5.7	0.201	0.224
T1	0.8	1.6	0.031	0.063
d	–	0.3	–	0.012
H1	2.0	2.4	0.079	0.094
H	2.1	2.5	0.083	0.098
L	4.0	4.7	0.157	0.185

Packaging Tape - SMB



SYMBOL	MILLIMETER
A0	3.60±0.1
B0	5.45±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.30±0.1
P	8.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.22±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	3000PCS

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